AUK Semiconductor

SMK1360CI

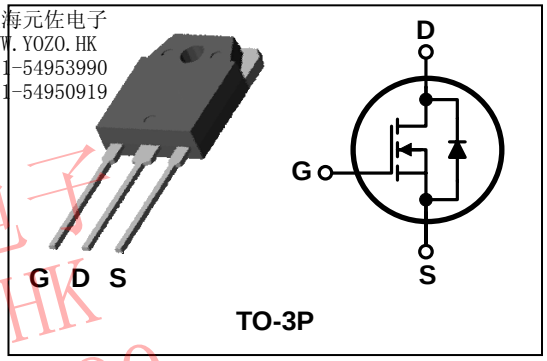
Advanced N-Ch Power MOSFET

SWITCHING REGULATOR APPLICATIONS

Features

- High Voltage: BV_{DSS}=600V(Min.)
- Low C_{rss} : C_{rss}=14.6pF(Typ.)
- Low gate charge : Qg=41nC(Typ.)
- Low $R_{DS(on)}$:$R_{DS(on)}$=0.65Ω(Max.)

PIN Connection



Ordering Information

Type No.	Marking	Package Code
SMK1360CI	SMK1360	TO-3P

Absolute maximum ratings (T_C=25°C unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Drain-source voltage	V_{DSS}		600	V
Gate-source voltage	V_{GSS}		±30	V
Drain current (DC)*	I_D	(Tc=25℃)	13	A
		(Tc=100℃)	8.2	A
Drain current (Pulsed)*	I_{DM}		52	A
Drain power dissipation	P_D		200	W
Avalanche current (Single) ②	I_{AS}		13	A
Single pulsed avalanche energy ②	E_{AS}		544	mJ
Avalanche current (Repetitive) ①	I_{AR}		13	A
Repetitive avalanche energy ①	E_{AR}		11.6	mJ
Junction temperature	T_J		150	°C
Storage temperature range	T_{stg}		-55~150	

* Limited by maximum junction temperature

Characteristic		Symbol	Typ.	Max	Unit
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	0.625	℃/W
	Junction-ambient	$R_{th(J-a)}$	-	40	

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Electrical Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	I_D=250μA, V_{GS}=0	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	I_D=250μA, V_{DS}= V_{GS}	2.0	-	4.0	V
Drain-source cut-off current	I_{DSS}	V_{DS}=600V, V_{GS}=0V	-	-	1	μA
		V_{DS}=480V, V_{GS}=0V T_C=125℃			100	
Gate leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±30V	-	-	±100	nA
Drain-source on-resistance ④	$R_{DS(ON)}$	V_{GS}=10V, I_D=6.5A	-	0.55	0.65	Ω
Forward transfer conductance ④	g_{fs}	V_{DS}=10V, I_D=6.5A	-	10	-	S
Input capacitance	Ciss	V_{GS}=0V, V_{DS}=25V f=1MHz	-	2162	2882	pF
Output capacitance	Coss		-	183	244	
Reverse transfer capacitance	Crss		-	14.6	19.4	
Turn-on delay time	$t_{d(on)}$	V_{DD}=300V, I_D=13A R_G=25Ω ③④	-	30	-	ns
Rise time	t_r		-	85	-	
Turn-off delay time	$t_{d(off)}$		-	140	-	
Fall time	t_f		-	90	-	
Total gate charge	Q_g	V_{DS}=480V, V_{GS}=10V I_D=13A ③④	-	41	63	nC
Gate-source charge	Q_{gs}		-	13	-	
Gate-drain charge	Q_{gd}		-	10.5	-	

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	13	A
Source current (Pulsed) ①	I_{SM}		-	-	52	
Forward voltage ④	V_{SD}	V_{GS}=0V, I_S=13A	-	-	1.4	V
Reverse recovery time	t_{rr}	I_s=13A, V_{GS}=0, di_S/dt=100A/ us	-	510	-	ns
Reverse recovery charge	Q_{rr}		-	4.3	-	uC

Note ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

② L=5.9mH, I_{AS}=13A, V_{DD}=50V, R_G=25Ω , Starting T_J = 25℃

③ Pulse Test : Pulse Width < 300us, Duty cycle≤ 2%

④ Essentially independent of operating temperature

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Electrical Characteristic Curves

Fig. 1 I_D - V_{DS}

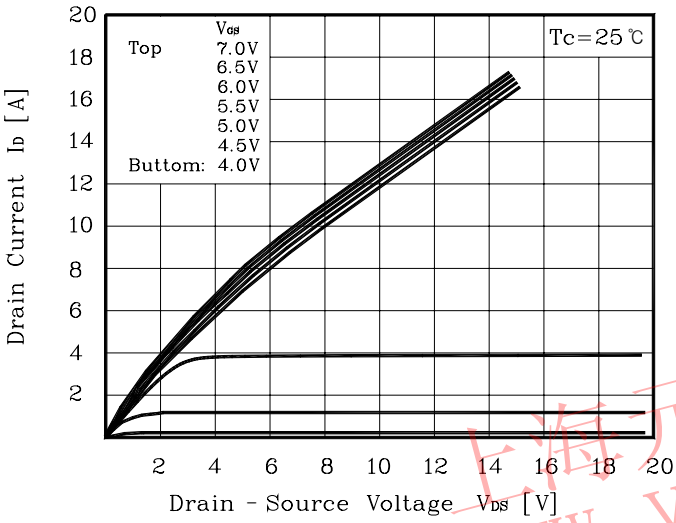


Fig. 2 I_D - V_{GS}

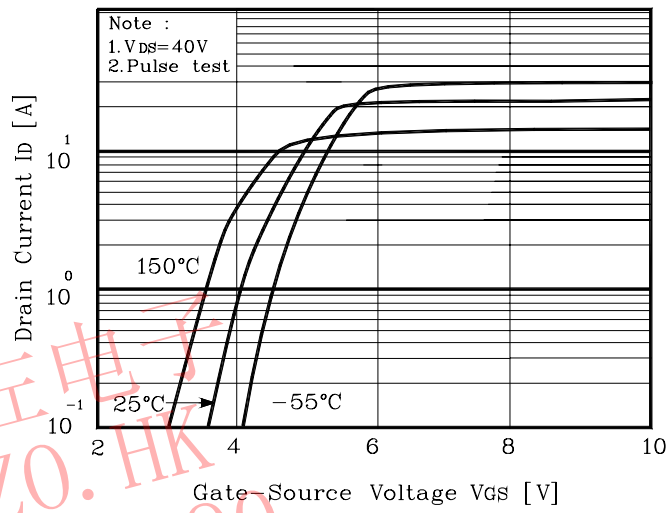


Fig. 3 $R_{DS(on)}$ - I_D

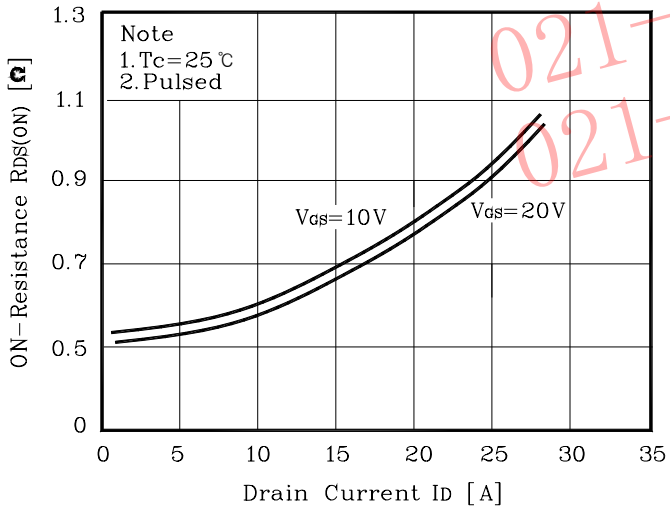


Fig. 4 I_S - V_{SD}

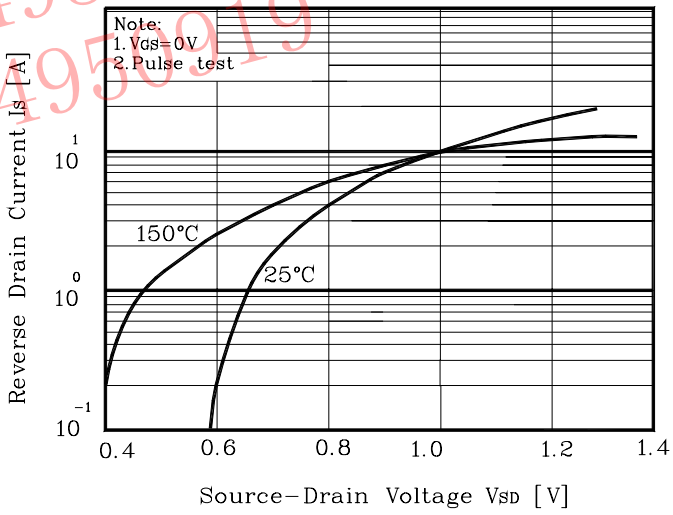


Fig. 5 Capacitance - V_{DS}

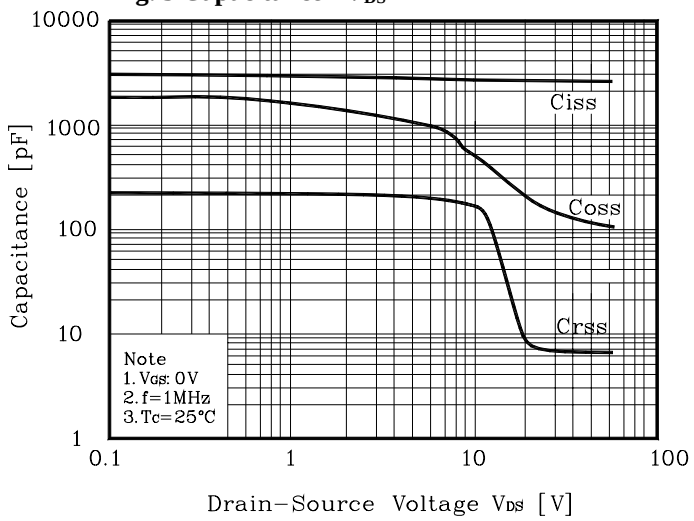
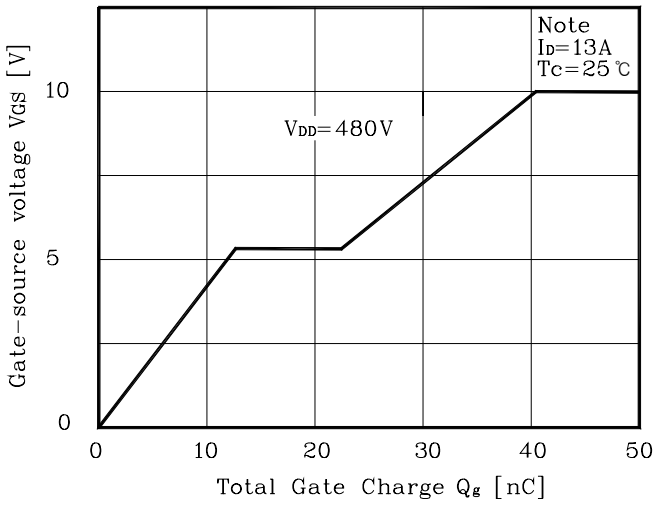


Fig.6 V_{GS} - Q_G



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Electrical Characteristic Curves

Fig. 7 V_{DSS} - T_J

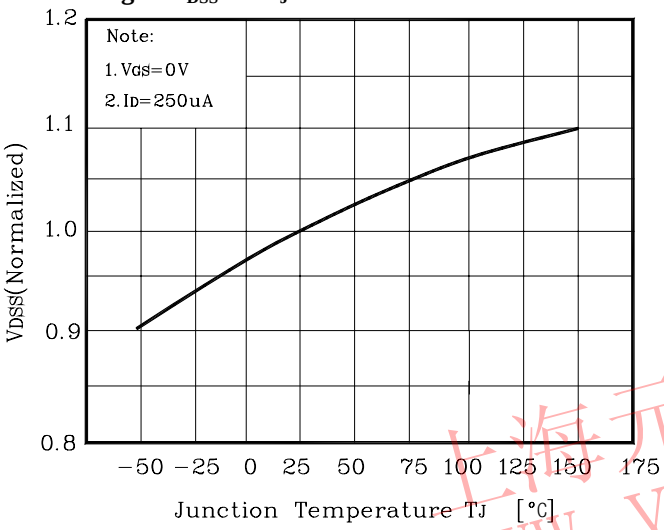

Fig.8 $R_{DS(on)}$ - T_J

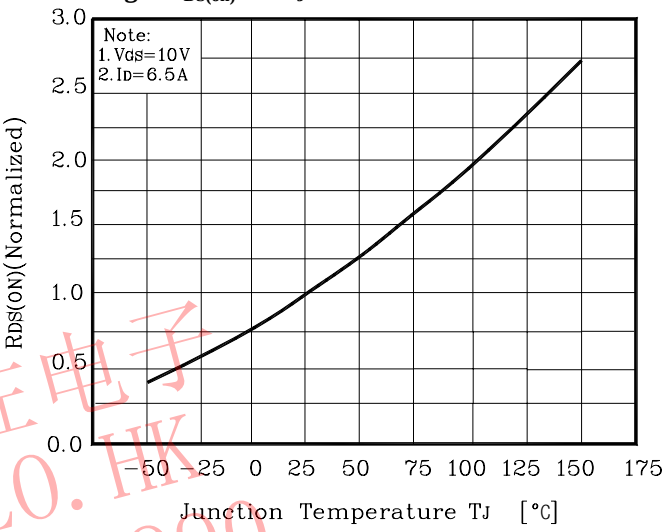

Fig. 9 I_D - T_C

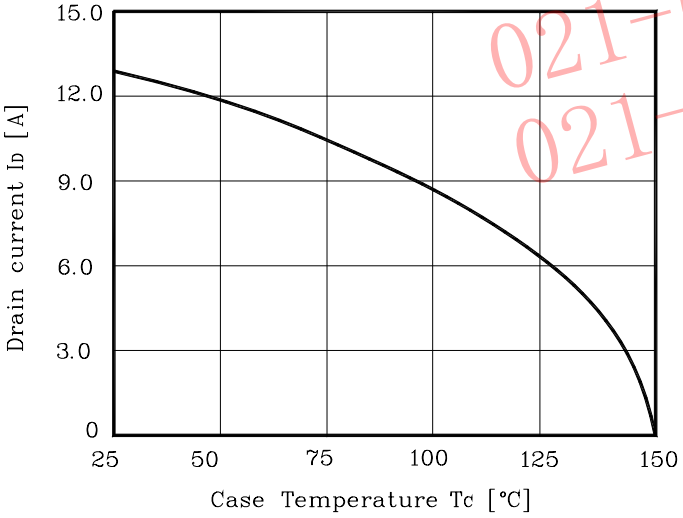

Fig. 10 Safe Operating Area

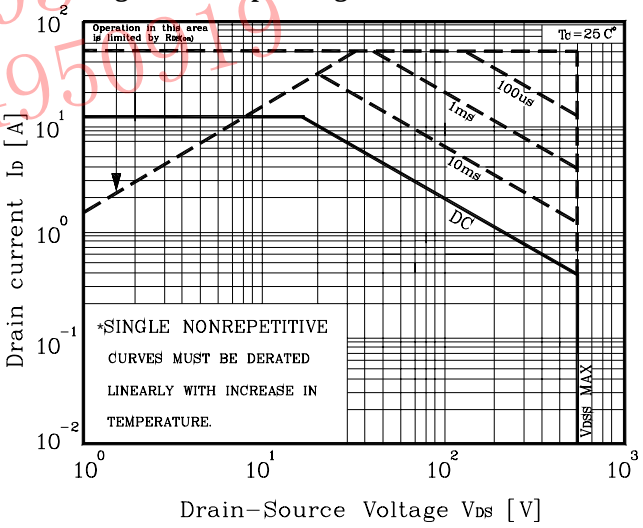

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Fig. 10 Gate Charge Test Circuit & Waveform

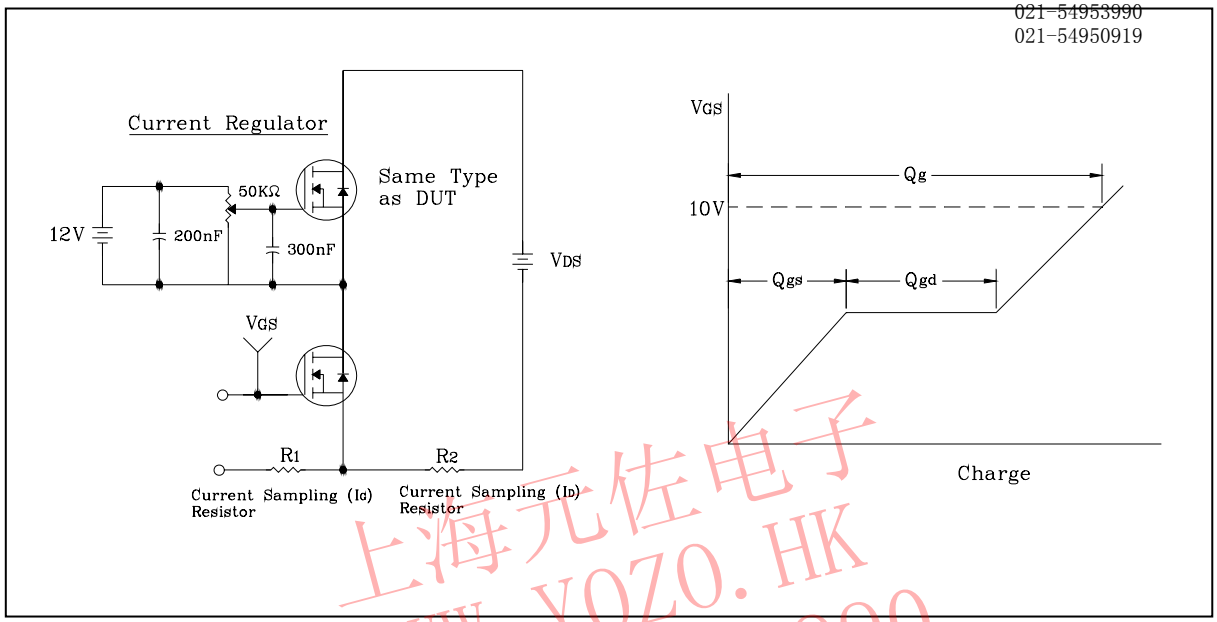

Fig. 11 Resistive Switching Test Circuit & Waveform

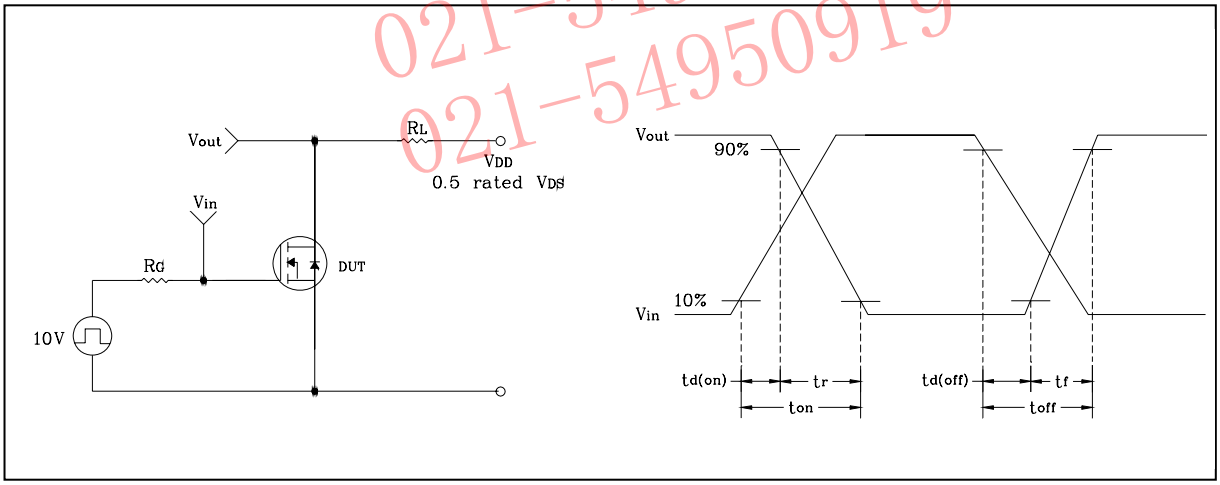

Fig. 12 E_{AS} Test Circuit & Waveform

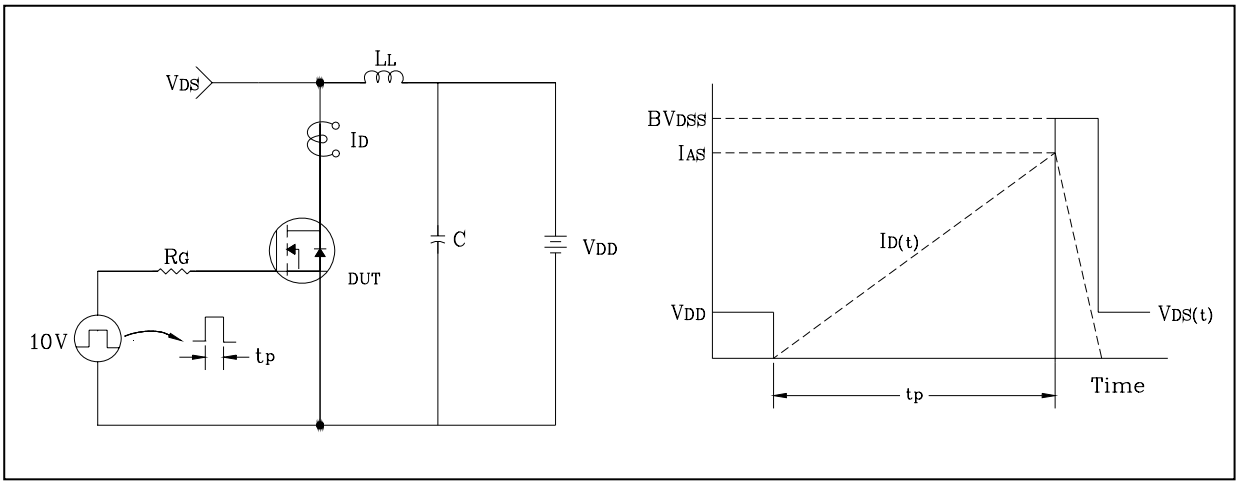

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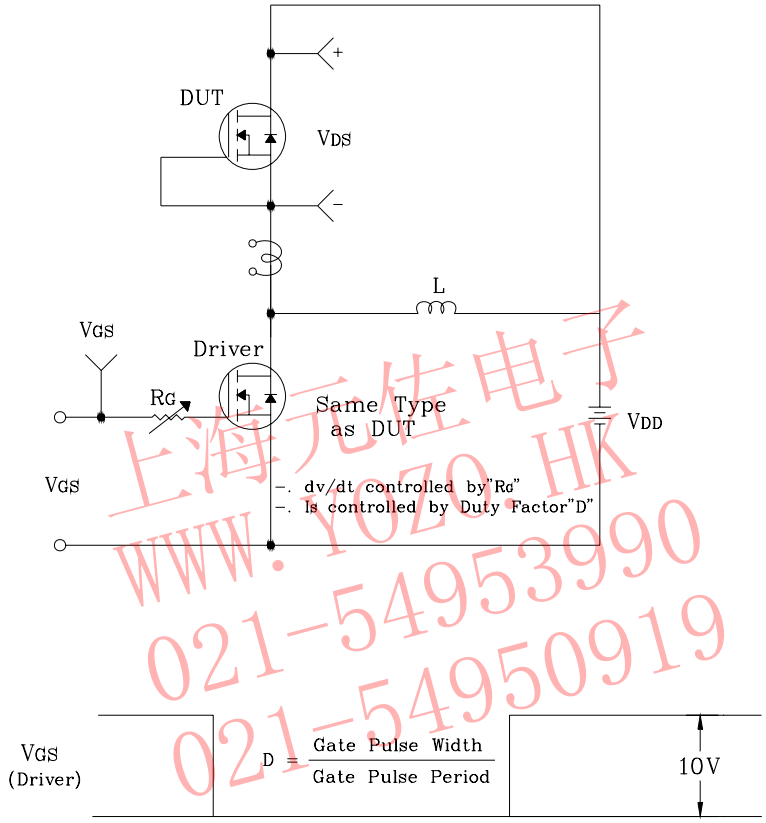
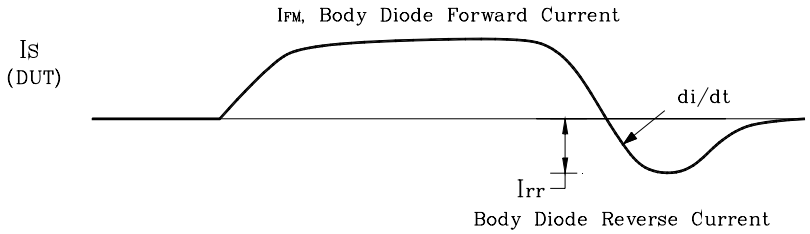
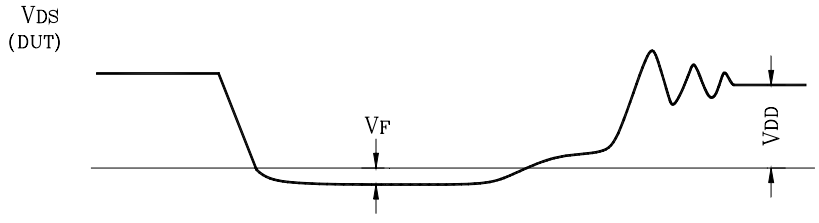
Fig. 13 Diode Reverse Recovery Time Test Circuit & Waveform







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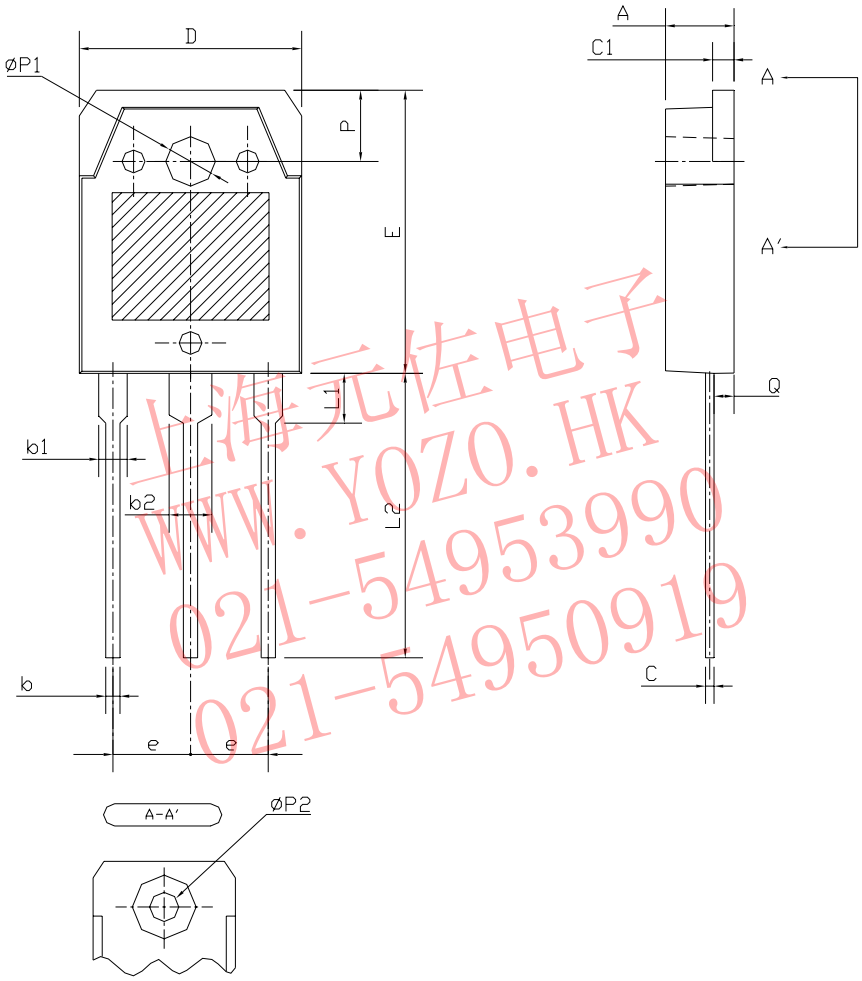
Outline Dimension



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
C	0.55	0.60	0.75
C1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
P	4.80	5.00	5.20
øP1	3.30	3.40	3.50
øP2		(3.20)	
Q	1.20	1.40	1.60

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